[NIKON-2205i14E2 CONFIG SHEET]

ITEM	TYPE	DETAIL
MODEL	Stepper / Scanner	NSR-2205i14E2
Main Body	Vintage	2006. 02
	Magnification	1/5 Reduction
	Light-Source	i-Line(365nm)
	Resolution	0.35um
	Variable Lens NA	0.50~0.63 Viriable
	Exposure Filed Size	22mq (up to 17.9H by 25.2V)
	Control	Bellows Unit
	Lens Adjust	Micrometer / PIEZO / Washer
	LAMP	2.5Kw Hg Lamp
	Holder Type	Pin(Low) Type
PC System	Hardware Type	AlphaServer DS15
	UPS System	No
	Software Version	MCSV 3.46C
		OS VMS 7.3-1
Alignment Sensor	LSA	Yes
	FIA	Yes
	LIA	No
	TTLFC2	Yes
	Measure Software	Yes
Illumination System	SHRINC Type	SHRINC4 Type
Interferometer System	Interferometer Type	5517C
	Wafer Stage	Yes
	Reticle Stage	Yes
Focus System	Single / Multi Focus	Multi Focus
Leveling System	Normal / Table	Table Leveling
Wafer Loader	Type1 / Type2 / Type3	Type3
	Wafer OF / Notch Type	Notch Type
	Wafer Size	8inch (200mm)
	Wafer Cassette	2 Cassette
	Wafer IN-Line	Left Type
	Wafer PRE-Align Type	NC PRE2
	Wafer Edge Exposure	No
Reticle Loader	Normal / SMIF Type	Normal
	Variable / Fixed	Fixed
	5 inch / 6 inch	6*0.25 inch
	Library / SLOT	3 Lib. (30Slot)
	Barder Reader	Yes
	Particle Checker	Yes
Control Rack	Type	Right Type
	Cable Length	Normal
Signal Tower	3 Color / 4 Color Type	3 Color Type
Chamber	ASAHI/SENDAI Type	ASAHI
	Model	N4A-C
	S/N	
	Single / CVCF NEMA	CVCF NEMA
	Electrical Power Spec	200/208~V, 50/60Hz, 3-Phase

	Item	Target Spec		Note
1	Resolution	≦0.35um		
2	Long Term Focus Stability	Within ±0.2um	0.4um pattern(CE) Average Value from previous days="3" 0.4um	
3	Magnification Control vs. Lens Heating	Within 0.02um	NIKON standard LC Test Condition (Heat & Cool Test)	
4	Auto focus repeatability	±0.1um		
5	Total Focus Deviation	≦0.35um	0.4um V/H pattern 5pts 0.4um V/H 5	
6	Lens distortion	Within ±0.05um		
7	Max expose field	22.0×22.0mm	3 days measurement 3	
8	Reticle blind setting accuracy	+0.4 to +0.8mm on reticle	NIKON standard Test Condition	
9	Exposure power	≥650mw/cm^2	new lamp	
10	Integrated exposure control	within ± 1.0%	input time: 100msec 200msec 400msec	
11	Illumination uniformity	Within 1.4%	3 times measurement with exposure area	

No.	Item	Target Spec	Condition	Note
12	Reticle rotation	$\|M\|+3\sigma \leqslant 20um$	Nikon slandard Test condition Nikon	
13	Array orthogonality	Within ± 0.1sec	After software compensation	
14	Stepping precision	Within 0.45um(3σ)	Nikon standard test	
15	Alignment accuracy (1) LSA (2) FIA	(1) $\|M\|+3\sigma \leqslant 0.06$ (2) $\|M\|+3\sigma \leqslant 0.065$	10 points EGA	
16	Stepping rate	27sec or less (150mm)	Exposure time: 130msec	
17	Wafer pre-alignment 2 repeatability	3σ <15um	20 times measurement for x, y and θ on same wafer	
18	Chip leveling accuracy	Within ± 1.5sec	10 times measurement	
19	Wafer System Operation Test	$\geqslant 99\%$	200Wafers	
20	Reticle System Operation Test	100%	Each 1 time for every slot	
21	Wafer flatness	$\leqq 2.5$um	Nikon standard test	